

#### Description

The AP7176B is a 3.0A ultra low-dropout (LDO) linear regulator that features an enable input and a power-good output.

The enable input and power-good output allow users to configure power management solutions that can meet the sequencing requirements of FPGAs, DSPs, and other applications with different startup and power-down requirements.

The AP7176B features two supply inputs, for power conversion supply and control. With the separation of the control and the power input very low dropout voltages can be reached and power dissipation is reduced.

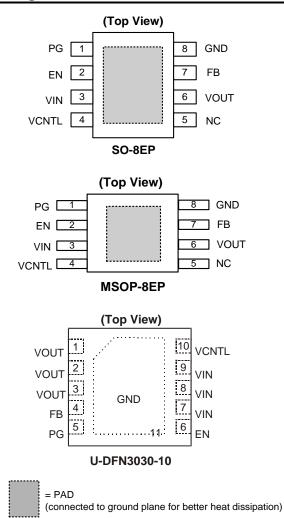
A precision reference and feedback control deliver 1.5% accuracy over load, line, and operating temperature ranges.

The AP7176B is available in SO-8EP, MSOP-8EP and U-DFN3030-10 packages with an exposed PAD to reduce the junction to case resistance and extend the temperature range it can be used in.

#### Features

- VIN Range: 1.2V to 3.65V, VCNTL 3.0V to 5.5V
- Adjustable Output Voltage
- Continuous Output Current IOUT = 3A
- Fast Transient Response
- Power-On-Reset Monitoring on VCNTL and VIN
- Internal Soft-Start
- Stable with Low ESR MLCC Capacitors
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

#### **Pin Assignments**



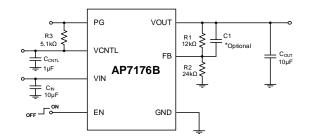
### Applications

- Notebooks
- PCs
- Netbooks
- Wireless communication
- Servers
- Motherboards
- Dongles
- Front side bus VTT (1.2V/3.3A)

- Notes:
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
  - Lead-free.
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



## **Typical Applications Circuit**

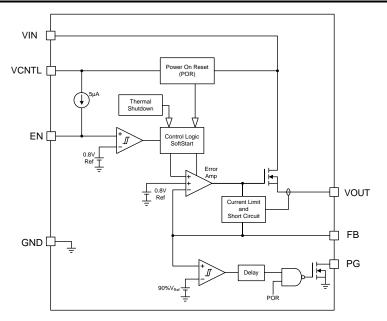




## **Pin Descriptions**

Pin		Pin Numbe	r	Function
Name	SO-8EP	MSOP-8EP	U-DFN3030-10	Function
PG	1	1	5	Power-Good. Output open drain to indicate the status of $V_{OUT}$ via monitoring the FB pin. This pin is pulled low when the voltage is outside the limits, during thermal shutdown and if either $V_{CNTL}$ or $V_{IN}$ goes below their thresholds.
EN	2	2	6	Enable pin. Driving this pin low will disable the part. When left floating an internal current source will pull this pin high and enable it.
VIN	3	3	7, 8, 9	Power input pin for current supply. Connect a decoupling capacitor ( $\geq 10\mu$ F) as close as possible to the pin for noise filtering.
VCNTL	4	4	10	BIAS supply for the controller, recommended 5V. Connect a decoupling capacitor $(\geq 1\mu F)$ as close as possible to the pin for noise filtering.
NC	5	5	—	No connection
VOUT	6	6	1, 2, 3	Power output pin
FB	7	7	4	Feedback to set the output voltage via an external resistor divider between VOUT and GND
GND	8	8	11	Ground
PAD	EP	EP	EP	Exposed pad connected to GND for good thermal conductivity.

### **Functional Block Diagram**





Symbol	Parameter	Rating	Unit
VIN	VIN Supply Voltage (VIN to GND)	-0.3 to +4.0	V
V <sub>CNTL</sub>	VCNTL Supply Voltage (VCNTL to GND)	-0.3 to +7.0	V
Vout	VOUT to GND Voltage	-0.3 to V <sub>IN</sub> +0.3	V
_	PG to GND Voltage	-0.3 to +7.0	V
_	EN, FB to GND Voltage	-0.3 to V <sub>CNTL</sub> +0.3	V
	Power Dissipation (SO-8EP)	1.7	
PD Power Dissipation (MSOP-8EP)		1.5	W
	Power Dissipation (U-DFN3030-10)	1.9	
TJ	Maximum Junction Temperature	+150	°C
TSTG	Storage Temperature	-65 to +150	°C
TSDR	Maximum Lead Soldering Temperature, 10 Seconds	+260	°C

#### Absolute Maximum Ratings (Note 4) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Note: 4. Stresses greater than those listed under *Absolute Maximum Ratings* can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to *Absolute Maximum Ratings* for extended periods can affect device reliability.

#### Recommended Operating Conditions (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Test Condition	Range	Unit
VCNTL	VCNTL Supply Voltage		3.0 to 5.5	V
VIN	VIN Supply Voltage		1.2 to 3.65	V
Vout	VOUT Output Voltage (when VCNTL -	0.8 to VIN - VDROP	V	
Іоит	VOUT Output Current		0 to 3	А
		IOUT = 3A at 25% nominal VOUT	8 to 1100	
COUT	VOUT Output Capacitance	I <sub>OUT</sub> = 2A at 25% nominal V <sub>OUT</sub>	8 to 1700	μF
		IOUT = 1A at 25% nominal VOUT	8 to 2400	
Esrcout	ESR of VOUT Output Capacitor		0 to 200	mΩ
T <sub>A</sub>	Ambient Temperature		-40 to +85	°C
TJ	Junction Temperature		-40 to +125	°C

**Electrical Characteristics** (Specifications apply over  $V_{CNTL} = 5V$ ,  $V_{IN} = 1.8V$ ,  $V_{OUT} = 1.2V$  and  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ , typical values  $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Sumbol	Denometer	Conditions	AP7176B			l lucit	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
SUPPLY CURRENT	SUPPLY CURRENT						
IVCNTL	VCNTL Supply Current	EN = VCNTL, IOUT = 0A	_	1.0	1.5	mA	
Isp	VCNTL Supply Current at Shutdown	EN = GND	_	15	30	μA	
130	VIN Supply Current at Shutdown	EN = GND, V <sub>IN</sub> = 3.65V	—	—	1	μA	
POWER-ON RESET (I	POR)		-				
VPOR_Rising (VCNTL)	Rising VCNTL POR Threshold	—	2.50	2.70	2.95	V	
VPOR_Hysteresis (VCNTL)	VCNTL POR Hysteresis	_	—	0.4	_	V	
VPOR_Rising (VIN)	Rising VIN POR Threshold	—	0.8	0.9	1.0	V	
VPOR_Hys (VIN)	VIN POR Hysteresis	—	—	0.5	—	V	



# **Electrical Characteristics** (continued) (Specifications apply over $V_{CNTL} = 5V$ , $V_{IN} = 1.8V$ , $V_{OUT} = 1.2V$ and $T_A = -40^{\circ}C$ to $+85^{\circ}C$ , typical values $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Symbol	Parameter		Conditio	ne		AP7176B		Unit
Symbol	Parameter		Conditio	ns	Min	Тур	Max	Unit
Ουτρυτ να	OLTAGE							
	Reference Voltage	FB = V <sub>OUT</sub>			—	0.8	—	V
	Output Voltage Accuracy		$V_{CNTL}$ = 3.0V to 5.5V, $I_{OUT}$ = 0A to 3A T <sub>J</sub> = -40°C to +125°C		-1.5		+1.5	%
Vref	Load Regulation	Iout = 0A to 3A   Iout = 10mA, Vcntl = 3.0V to 5.5V		_	0.06	0.25	%	
	Line Regulation			-0.15		+0.15	%/V	
	VOUT Pull-Low Resistance	$V_{CNTL} = 3.3V$ ,	V <sub>CNTL</sub> = 3.3V, V <sub>EN</sub> = 0V, V <sub>OUT</sub> < 0.8V			10	_	Ω
	FB Input Current	V <sub>FB</sub> = 0.8V			-100	_	+100	nA
DROPOUT	VOLTAGE							
			$\lambda = 2 E \lambda$	$T_J = +25^{\circ}C$	—	0.33	0.38	
			$V_{OUT} = 2.5V$	$T_J = -40^{\circ}C \text{ to } +125^{\circ}C$	_	_	0.53	
	VIN-to-VOUT Dropout Voltage	VCNTL = 5.0V		T <sub>J</sub> = +25°C	—	0.31	0.36	v
Vdrop	(Note 5)	Iout = 3A	Vout = 1.8V	$T_J = -40^{\circ}C \text{ to } +125^{\circ}C$	—	-	0.50	v
			V <sub>OUT</sub> = 1.2V	T <sub>J</sub> = +25°C	_	0.30	0.35	
		V <sub>OUT</sub> = 1.		T <sub>J</sub> = -40°C to +125°C	_	_	0.48	
L	Current Limit Lough	TJ = +25°C, Vo	OUT = 80% VNON	IINAL	4.5	5.7	6.7	А
ILIM	Current-Limit Level	$T_J = -40^{\circ}C$ to +	-125°C		4.2	_	_	А
PROTECTIO	ONS							
ISHORT	Short Current-Limit Level	VFB < 0.2V			1.1		А	
Tsd	Thermal Shutdown Temperature	T <sub>J</sub> rising		_	+170	_	°C	
T <sub>SD_HYS</sub>	Thermal Shutdown Hysteresis	—			_	+50	_	°C
ENABLE A	ND SOFT-START							
EN_HI	EN Logic High Threshold Voltage	VEN rising		0.5	0.8	1.1	V	
EN_Hys	EN Hysteresis	—			_	0.1	—	V
I_EN	EN Pull-High Current	EN = GND		_	5	_	μA	
tss	Soft-Start Interval	_			0.3	0.6	1.2	ms
t_delay	Turn-On Delay	From being en	abled to Vour r	sing 10%	200	350	500	μs
POWER-GO	DOD AND DELAY							
VTHPG	Rising PG Threshold Voltage	V <sub>FB</sub> rising			90	92	95	%
VPG_Hys	PG Threshold Hysteresis	_				8		%
VPG_Low	PG Pull-Low Voltage	PG sinks 5mA			_	0.25	0.4	V
tPG_Deb	PG Debounce Interval	VFB < falling PG voltage threshold		nold		10		μs
t_PGDEL	PG Delay Time	From VFB = VTHPG to rising edge of the VPG		1	2	4	ms	
THERMAL	CHARACTERISTIC							
		SO-8EP (Note	6)		_	70		°C/W
θја	Thermal Resistance Junction-to- Ambient	MSOP-8EP (N	lote 7)		_	80	_	°C/W
		U-DFN3030-1	0 (Note 6)		_	60	_	°C/W
		SO-8EP (Note	6)		_	30	_	°C/W
θις	Thermal Resistance Junction-to- Case	MSOP-8EP (N	lote 7)		_	30		°C/W
		U-DFN3030-10 (Note 6)			_	20		°C/W

Notes: 5. Dropout voltage is the voltage difference between the input and the output at which the output voltage drops 2% below its nominal value. 6. Device mounted on 2" x 2" FR-4 substrate PC board, 2oz copper, with minimum recommended pad on top layer and thermal vias to bottom layer ground

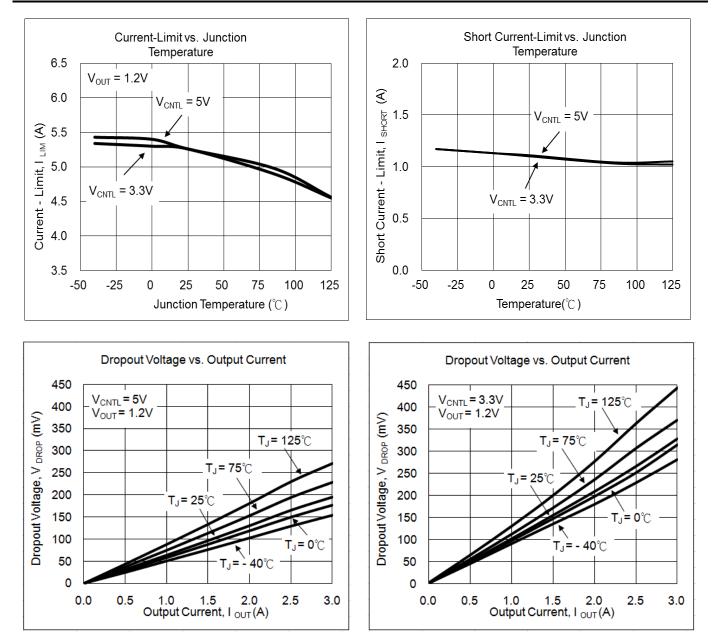
plane.

7. Device mounted on 2" x 2" FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



AP7176B

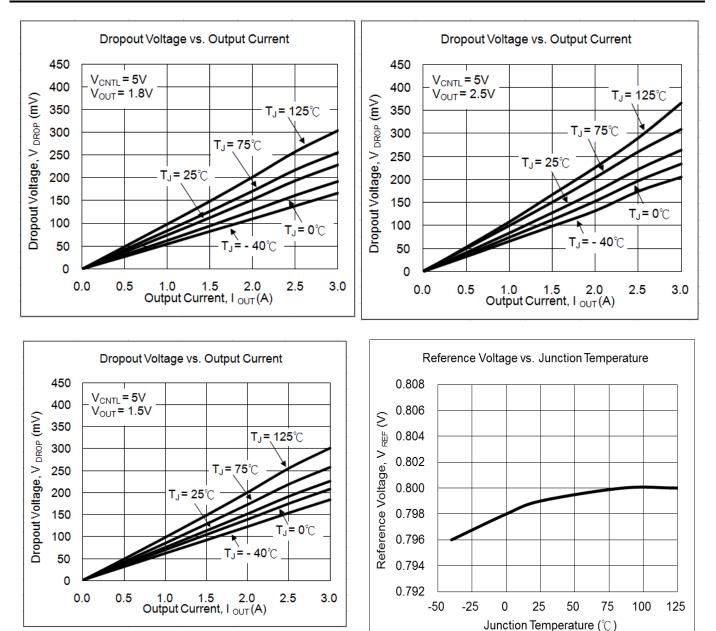
### **Typical Characteristics**





AP7176B

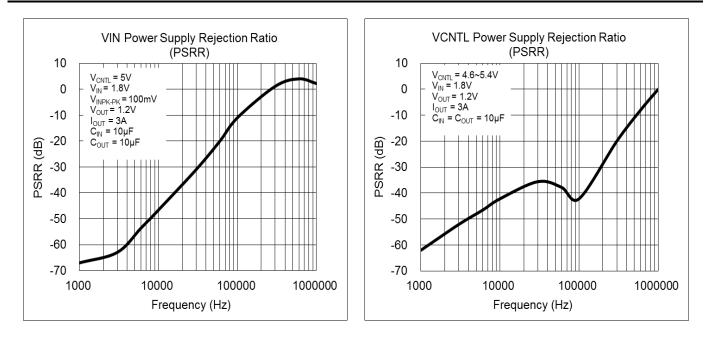
### Typical Characteristics (continued)





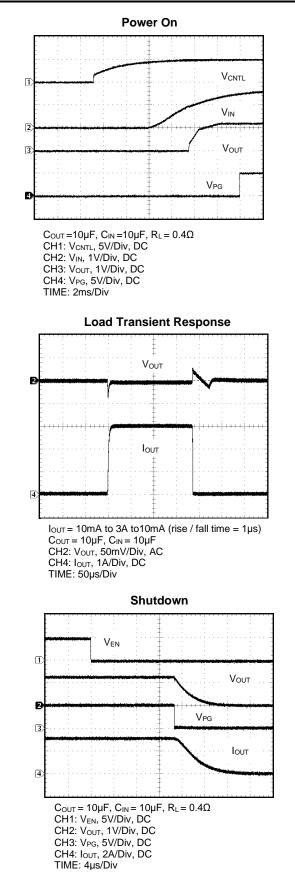
AP7176B

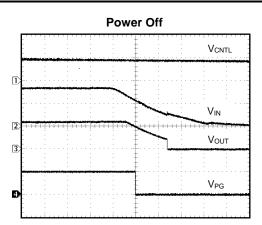
### Typical Characteristics (continued)



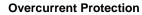


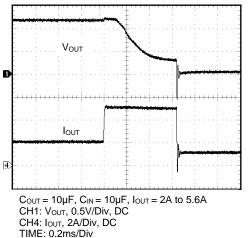
## **Operating Waveforms** (Test Conditions VIN = 1.8V, VCNTL = 5V, VOUT 1.2V, TA = +25°C unless otherwise specified.)

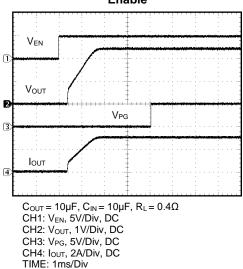




 $\begin{array}{l} C_{OUT}=10\mu F,\ C_{IN}=10\mu F,\ R_L=0.4\Omega\\ CH1:\ V_{CNTL},\ 5V/Div,\ DC\\ CH2:\ V_{IN},\ 1V/Div,\ DC\\ CH3:\ V_{OUT},\ 1V/Div,\ DC\\ CH4:\ V_{PG},\ 5V/Div,\ DC\\ TIME:\ 2ms/Div\\ \end{array}$ 











#### **Application Information**

#### Power-Good and Delay

AP7176B monitors the feedback voltage V<sub>FB</sub> on the FB pin. An internal delay timer is started after the PG voltage threshold (V<sub>THPG</sub>) on the FB pin is reached. At the end of the delay time an internal nMOS of the PG is turned off to indicate that the power at the output is good (PG). This monitoring function is continued during operation and if V<sub>FB</sub> falls 8% (typ) below V<sub>THPG</sub>, the nMOS of the PG is turned on after a delay time of typical 10µs to avoid oscillating of the PG signal.

#### **Power-On Reset**

AP7176B monitors both supply voltages, V<sub>CNTL</sub> and V<sub>IN</sub> to ensure operation as intended. A Soft-Start process is initiated after both voltages exceed their POR threshold during power on. During operation the POR component continues to monitor the supply voltage and pulls the PG low to indicate an out of regulation supply. This function will engage without regard to the status of the output.

#### Soft-Start

AP7176B incorporates an internal Soft-Start function. The output voltage rise is controlled to limit the current surge during startup. The typical Soft-Start time is 0.6ms

#### **Current-Limit Protection**

AP7176B monitors the current flow through the nMOS and limits the maximum current to avoid damage to the load and AP7176B during overload conditions.

#### **Short-Circuit Current-Limit Protection**

AP7176B incorporates a current-limit function to reduce the maximum current to 1.1A (typ) when the voltage at FB falls below 0.2V (typ) during an overload or short-circuit situation.

During startup period, this function is disabled to ensure successful heavy load startup.

#### **Enable Control**

If the enable pin (EN) is left open, an internal current source around 5µA pulls the pin up and enables the AP7176B. This will reduce the bill of material saving an external pullup resistor. Driving the enable pin low disables the device. Driving the pin high subsequently initiates a new Soft-Start cycle.

#### **Output Voltage Regulation**

Output Voltage is set by resistor divider from V<sub>OUT</sub> via FB pin to GND. Internally V<sub>FB</sub> is compared to a 0.8V temperature compensated reference voltage and the nMOS pass element regulates the output voltage while delivering current from VIN to VOUT.

#### Setting the Output Voltage

A resistor divider connected to FB pin programs the output voltage.

$$V_{OUT} = V_{REF} * \left(1 + \frac{R1}{R2}\right) V$$

R1 is connected from VOUT to FB with Kelvin sensing connection. R2 is connected from FB to GND. To improve load transient response and stability, a bypass capacitor can be connected in parallel with R1. (optional in typical application circuit)

#### **Power Sequencing**

AP7176B requires no specific sequencing between VIN and VCNTL. However, care should be taken to avoid forcing VOUT for prolonged times without the presence of VIN. Conduction through internal parasitic diode (from VOUT to VIN) could damage AP7176B.

#### Thermal Shutdown

The PCB layout and power requirements for AP7176B under normal operation condition should allow enough cooling to restrict the junction temperature to +125°C. The packages for AP7176B have an exposed PAD to support this. These packages provide better connection to the PCB and thermal performance. Refer to the *Layout Consideration*.

If AP7176B junction temperature reaches +170°C a thermal protection block disables the nMOS pass element and lets the part cool down. After its junction temperature drops by 50°C (typ), a new Soft-Start cycle will be initiated. A new thermal protection will start, if the load or ambient conditions continue to raise the junction temperature to +170°C. This cycle will repeat until normal operation temperature is maintained again.

9 of 15 www.diodes.com AP7176B



#### Application Information (continued)

#### Output Capacitor

An output capacitor (C<sub>OUT</sub>) is needed to improve transient response and maintain stability. The ESR (equivalent series resistance) and capacitance drives the selection. Care needs to be taken to cover the entire operating temperature range.

The output capacitor can be an Ultra-Low-ESR ceramic chip capacitor or a low ESR bulk capacitor like a solid tantalum, POSCap or aluminum electrolytic capacitor.

COUT is used to improve the output stability and reduces the changes of the output voltage during load transitions. The slew rate of the current sensed via the FB pin in AP7176B is reduced. If the application has large load variations, it is recommended to utilize low-ESR bulk capacitors.

It is recommended to place ceramic capacitors as close as possible to the load and the ground pin and care should be taken to reduce the impedance in the layout.

#### **Input Capacitor**

To prevent the input voltage from dropping during load steps it is recommended to utilize an input capacitor (C<sub>IN</sub>). As with the output capacitor the following are acceptable, Ultra-Low-ESR ceramic chip capacitor or low ESR bulk capacitor like a solid tantalum, POSCap or aluminum electrolytic capacitor. Typically, it is recommended to utilize a capacitance of at least 10µF to avoid output voltage drop due to reduced input voltage. The value can be lower if V<sub>IN</sub> changes are not critical for the application.

#### Layout Consideration

For good ground loop and stability, the input and output capacitors should be located close to the input, output, and ground pins of the device. No other application circuit is connected within the loop. Avoid using vias within ground loop. If vias must be used, multiple vias should be used to reduce via inductance.

The regulator ground pin should be connected to the external circuit ground to reduce voltage drop caused by trace impedance. Ground plane is generally used to reduce trace impedance.

Wide trace should be used for large current paths from VIN to VOUT, and load circuit.

Place the R1, R2, and C1 (optional) near the LDO as close as possible to avoid noise coupling.

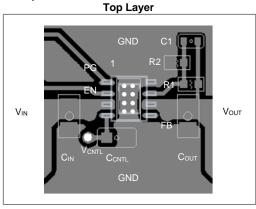
R2 is placed close to device ground. Connect the ground of the R2 to the GND pin by using a dedicated trace.

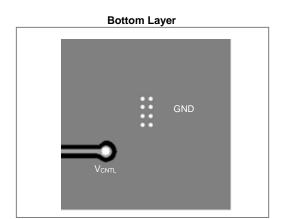
Connect the pin of the R1 directly to the load for Kelvin sensing.

No high current should flow through the ground trace of feedback loop and affect reference voltage stability.

For the packages with exposed pads, heat sinking is accomplished using the heat spreading capability of the PCB and its copper traces. Suitable PCB area on the top layer and thermal vias (0.3mm drill size with 1mm spacing, 4 to 8 vias at least) to the VIN power plane can help to reduce device temperature greatly.

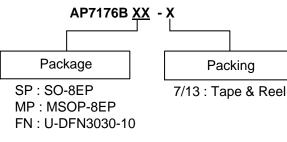
#### Reference Layout Plots:







### **Ordering Information**



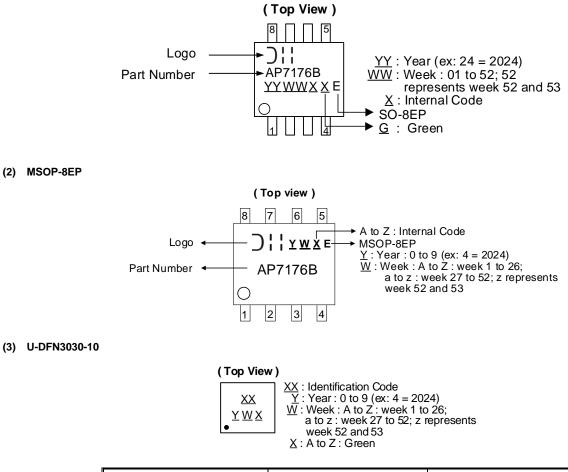
-8EP		
13030-10		

Packing

Orderable Part Number	Baakaga Cada	Paakaga	Packing		
	erable Part Number Package Code	Package	Qty.	Carrier	
AP7176BSP-13	SP	SO-8EP	2500	Tape & Reel	
AP7176BMP-13	MP	MSOP-8EP	2500	Tape & Reel	
AP7176BFN-7	FN	U-DFN3030-10	3000	Tape & Reel	
AP7176BFN-13	FN	U-DFN3030-10	3000	Tape & Reel	

#### **Marking Information**

(1) SO-8EP

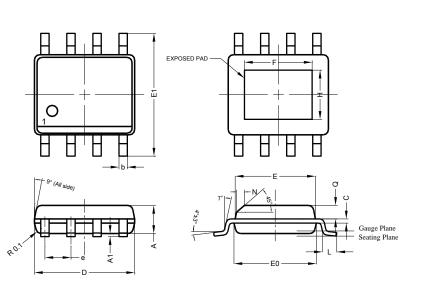


Orderable Part Number	Package	Identification Code
AP7176BFN-7	U-DFN3030-10	A7
AP7176BFN-13	U-DFN3030-10	Α7



### Package Outline Dimensions

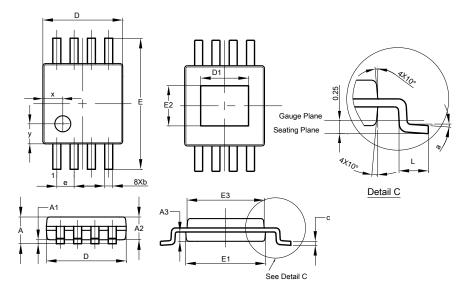
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SO-8	BEP	
Dim	Min	Max	Тур
Α	1.40	1.50	1.45
A1	0.00	0.13	-
b	0.30	0.50	0.40
С	0.15	0.25	0.20
D	4.85	4.95	4.90
Е	3.80	3.90	3.85
E0	3.85	3.95	3.90
E1	5.90	6.10	6.00
е	1	-	1.27
F	2.75	3.35	3.05
Н	2.11	2.71	2.41
L	0.62	0.82	0.72
N	-	-	0.35
q	0.60	0.70	0.65
All Di	mensi	ons in	mm

MSOP-8EP

SO-8EP

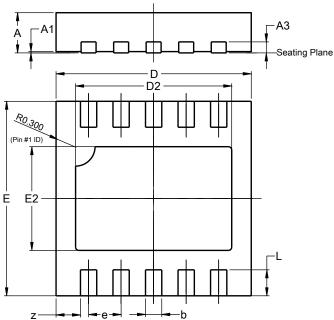


MSOP-8EP					
Dim	Min	Max	Тур		
Α	-	1.10	-		
A1	0.05	0.15	0.10		
A2	0.75	0.95	0.86		
A3	0.29	0.49	0.39		
b	0.22	0.38	0.30		
c	0.08	0.23	0.15		
D	2.90	3.10	3.00		
D1	1.60	2.00	1.80		
Е	4.70	5.10	4.90		
E1	2.90	3.10	3.00		
E2	1.30	1.70	1.50		
E3	2.85	3.05	2.95		
e	-	-	0.65		
L	0.40	0.80	0.60		
а	0°	8°	4°		
х	-	-	0.750		
У	-	-	0.750		
	Dimens	sions ii	n mm		



### Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

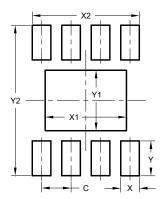


	U-DFN	3030-10	
Dim	Min	Max	Тур
Α	0.57	0.63	0.60
A1	0.00	0.05	0.02
A3			0.15
b	0.20	0.30	0.25
D	2.90	3.10	3.00
D2	2.30	2.50	2.40
Е	2.90	3.10	3.00
E2	1.50	1.70	1.60
е			0.50
L	0.25	0.55	0.40
z			0.375
All	Dimens	sions in	mm

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8EP



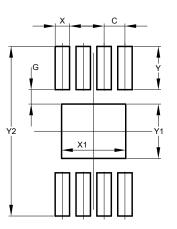
Dimensions	Value
Dimensions	(in mm)
С	1.270
Х	0.802
X1	3.502
X2	4.612
Y	1.505
Y1	2.613
Y2	6.500

U-DFN3030-10



### Suggested Pad Layout (continued)

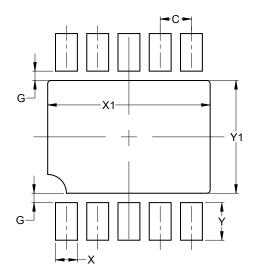
Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	0.450
Х	0.450
X1	2.000
Y	1.350
Y1	1.700
Y2	5.300

U-DFN3030-10

**MSOP-8EP** 



Dimensions	Value (in mm)
С	0.50
G	0.15
Х	0.35
X1	2.60
Y	0.60
Y1	1.80

#### **Mechanical Data**

- Moisture Sensitivity: Level 1 Per J-STD-020
- Terminals:
  - SO-8EP/MSOP-8EP: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
  - U-DFN3030-10: Finish NiPdAu over Copper Leads, Solderable per MIL-STD-202, Method 208 (4)
- Weight:
  - SO-8EP: 0.081 grams (Approximate)
  - MSOP-8EP: 0.026 grams (Approximate)
  - U-DFN3030-10: 0.01 grams (Approximate)



#### IMPORTANT NOTICE

1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.

3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.

4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.

Diodes' products are provided subject Diodes' Standard Terms and Conditions of to Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.

7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.

8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

9. This Notice may be periodically updated with the most recent version available at <a href="https://www.diodes.com/about/company/terms-and-conditions/important-notice">https://www.diodes.com/about/company/terms-and-conditions/important-notice</a>

The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. All other trademarks are the property of their respective owners. © 2024 Diodes Incorporated. All Rights Reserved.

#### www.diodes.com

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

**Diodes Incorporated:** 

AP7176BSP-13 AP7176BMP-13 AP7176BFN-7